Journal of Crystal Growth 96 (1989) 1036–1042
North-Holland, Amsterdam

AUTHOR INDEX

Abramof, E., S.O. Ferreira, C. Boschetti and I.N. Bandeira, Characterization of $Pb_{0.8}Sn_{0.2}Te$ films grown on KCl substrates by hot-wall epitaxy 96 (1989) 637
Acosta, D., see Piña 96 (1989) 685
Amelinckx, S., see Zandbergen 96 (1989) 716
Anderson, E.E., see Cheng 96 (1989) 756
Aslan, M., see Jaeger 96 (1989) 459
Astles, M.G., see Nouruzi-Khorasani 96 (1989) 348
Atherton, L.J., see Thomas 96 (1989) 135

Bąk-Misiuk, J., see Strupiński 96 (1989) 107
Balk, P., see Leiber 96 (1989) 483
Balk, P., see Westphalen 96 (1989) 982
Bandeira, I.N., see Abramof 96 (1989) 637
Barber, D.J., see Song 96 (1989) 985
Barns, R.L., see Brody 96 (1989) 225
Baronnet, A., see Sun 96 (1989) 265
Barreto, J., see Piña 96 (1989) 685
Bauser, E., see Nakada 96 (1989) 234
Bauser, E., see Nakada 96 (1989) 243
Bensahel, D., see Regolini 96 (1989) 505
Bertrand, O., N. Floquet and D. Jacquot, Growth of large $Mo_{18}O_{52}$ single crystals by a vapor phase method 96 (1989) 708
Bhatt, V.P., K. Gireesan and G.R. Pandya, Growth and characterization of SnSe and $SnSe_2$ single crystals 96 (1989) 649
Bilgram, J.H., M. Firmann and E. Hürlimann, Dendritic solidification of krypton and xenon 96 (1989) 175
Biloni, H., see De Cheveigné 96 (1989) 732
Bordui, P.F. and S. Motakef, Hydrodynamic control of solution inclusion during crystal growth of $KTiOPO_4$ (KTP) from high-temperature solution 96 (1989) 405
Bosacchi, A., S. Franchi, Yu.O. Kanter and S.I. Chikichev, Study of GaAs MBE growth under Ga-rich conditions by RHEED intensity oscillations 96 (1989) 899
Bosch, P., see Piña 96 (1989) 685
Boschetti, C., see Abramof 96 (1989) 637
Bose, S.S., see Lee 96 (1989) 27
Bostanov, V., see Obretenov 96 (1989) 843
Bouix, J., see Vincent 96 (1989) 871
Bourret, E.D., see Lee 96 (1989) 333
Boutellier, R., B.N. Sun, H.J. Scheel and H. Schmid, Flux separation in crystal growth of $YBa_2Cu_3O_{7-x}$ 96 (1989) 465
Brauers, A., see Leiber 96 (1989) 483
Brody, H.D., J.S. Haggerty, M.J. Cima, M.C. Flemings, R.L. Barns, E.M. Gyorgy, D.W. Johnson, W.W. Rhodes, W.A. Sunder and R.A. Laudise, Highly textured and single crystal $Bi_2CaSr_2Cu_2O_x$ prepared by laser heated float zone crystallization 96 (1989) 225
Brown, R.A., see Thomas 96 (1989) 135
Brown, R.A., see Patnaik 96 (1989) 153
Brown, R.A., see Kim 96 (1989) 609
Brush, L.N. and R.F. Sekerka, A numerical study of two-dimensional crystal growth forms in the presence of anisotropic growth kinetics 96 (1989) 419
Buchan, N.I., see Li 96 (1989) 906
Button, C., see Jones 96 (1989) 769

Camarillo, E., see Piña 96 (1989) 685
Capper, P., C.D. Maxey, P.A.C. Whiffin and B.C. Easton, Substrate orientation effects in $Cd_xHg_{1-x}Te$ grown by MOVPE 96 (1989) 519
Carlsson, J.-O., see Ottosson 96 (1989) 1019
Cassanho, A., D.R. Gabbe and H.P. Jenssen, Growth of single crystals of pure and Ce-doped Nd_2CuO_4 96 (1989) 999
Cazin-Bourguignon, A.-M. and S. Motakef, Thermoelastic analysis of GaAs in LEC growth configuration. IV. Effectiveness of top assembly and bottom heaters in control of stresses in low pressure systems 96 (1989) 390
Chadwick, B.K., Equilibrium analysis of the MOCVD $Ga(CH_3)_3$–AsH_3–H_2 system 96 (1989) 693
Chait, A., see Young 96 (1989) 65
Chaplain, R., see Guenais 96 (1989) 119
Chattopadhyay, K., see Swamy 96 (1989) 628
Chen, C.H., E.H. Reihlen and G.B. Stringfellow, OMVPE growth of GaAs using dimethylarsine 96 (1989) 497
Chen, Changkang and B.M. Wanklyn, Evaporation kinetics of a halide flux system for the growth of Bi–Sr–Ca–Cu–O superconducting crystals 96 (1989) 547
Chen, H.-C. and Y.-H. Xu, Growth and some properties of undoped and doped $(K_{1-x}Na_x)_{0.4}(Sr_{1-y}Ba_y)_{0.8}Nb_2O_6$ (KNSBN) single crystals with tungsten–bronze structure 96 (1989) 357
Chen, S.L., see Lee 96 (1989) 785
Chen Weidong, Lu Jian, Yu Meifang, Qiao

Journal of Crystal Growth 96 (1989) 1036–1042
North-Holland, Amsterdam

AUTHOR INDEX

Abramof, E., S.O. Ferreira, C. Boschetti and I.N. Bandeira, Characterization of $Pb_{0.8}Sn_{0.2}Te$ films grown on KCl substrates by hot-wall epitaxy 96 (1989) 637
Acosta, D., see Piña 96 (1989) 685
Amelinckx, S., see Zandbergen 96 (1989) 716
Anderson, E.E., see Cheng 96 (1989) 756
Aslan, M., see Jaeger 96 (1989) 459
Astles, M.G., see Nouruzi-Khorasani 96 (1989) 348
Atherton, L.J., see Thomas 96 (1989) 135

Bąk-Misiuk, J., see Strupiński 96 (1989) 107
Balk, P., see Leiber 96 (1989) 483
Balk, P., see Westphalen 96 (1989) 982
Bandeira, I.N., see Abramof 96 (1989) 637
Barber, D.J., see Song 96 (1989) 985
Barns, R.L., see Brody 96 (1989) 225
Baronnet, A., see Sun 96 (1989) 265
Barreto, J., see Piña 96 (1989) 685
Bauser, E., see Nakada 96 (1989) 234
Bauser, E., see Nakada 96 (1989) 243
Bensahel, D., see Regolini 96 (1989) 505
Bertrand, O., N. Floquet and D. Jacquot, Growth of large $Mo_{18}O_{52}$ single crystals by a vapor phase method 96 (1989) 708
Bhatt, V.P., K. Gireesan and G.R. Pandya, Growth and characterization of SnSe and $SnSe_2$ single crystals 96 (1989) 649
Bilgram, J.H., M. Firmann and E. Hürlimann, Dendritic solidification of krypton and xenon 96 (1989) 175
Biloni, H., see De Cheveigné 96 (1989) 732
Bordui, P.F. and S. Motakef, Hydrodynamic control of solution inclusion during crystal growth of $KTiOPO_4$ (KTP) from high-temperature solution 96 (1989) 405
Bosacchi, A., S. Franchi, Yu.O. Kanter and S.I. Chikichev, Study of GaAs MBE growth under Ga-rich conditions by RHEED intensity oscillations 96 (1989) 899
Bosch, P., see Piña 96 (1989) 685
Boschetti, C., see Abramof 96 (1989) 637
Bose, S.S., see Lee 96 (1989) 27
Bostanov, V., see Obretenov 96 (1989) 843
Bouix, J., see Vincent 96 (1989) 871
Bourret, E.D., see Lee 96 (1989) 333
Boutellier, R., B.N. Sun, H.J. Scheel and H. Schmid, Flux separation in crystal growth of $YBa_2Cu_3O_{7-x}$ 96 (1989) 465
Brauers, A., see Leiber 96 (1989) 483
Brody, H.D., J.S. Haggerty, M.J. Cima, M.C. Flemings, R.L. Barns, E.M. Gyorgy, D.W. Johnson, W.W. Rhodes, W.A. Sunder and R.A. Laudise, Highly textured and single crystal $Bi_2CaSr_2Cu_2O_x$ prepared by laser heated float zone crystallization 96 (1989) 225
Brown, R.A., see Thomas 96 (1989) 135
Brown, R.A., see Patnaik 96 (1989) 153
Brown, R.A., see Kim 96 (1989) 609
Brush, L.N. and R.F. Sekerka, A numerical study of two-dimensional crystal growth forms in the presence of anisotropic growth kinetics 96 (1989) 419
Buchan, N.I., see Li 96 (1989) 906
Button, C., see Jones 96 (1989) 769

Camarillo, E., see Piña 96 (1989) 685
Capper, P., C.D. Maxey, P.A.C. Whiffin and B.C. Easton, Substrate orientation effects in $Cd_xHg_{1-x}Te$ grown by MOVPE 96 (1989) 519
Carlsson, J.-O., see Ottosson 96 (1989) 1019
Cassanho, A., D.R. Gabbe and H.P. Jenssen, Growth of single crystals of pure and Ce-doped Nd_2CuO_4 96 (1989) 999
Cazin-Bourguignon, A.-M. and S. Motakef, Thermoelastic analysis of GaAs in LEC growth configuration. IV. Effectiveness of top assembly and bottom heaters in control of stresses in low pressure systems 96 (1989) 390
Chadwick, B.K., Equilibrium analysis of the MOCVD $Ga(CH_3)_3$–AsH_3–H_2 system 96 (1989) 693
Chait, A., see Young 96 (1989) 65
Chaplain, R., see Guenais 96 (1989) 119
Chattopadhyay, K., see Swamy 96 (1989) 628
Chen, C.H., E.H. Reihlen and G.B. Stringfellow, OMVPE growth of GaAs using dimethylarsine 96 (1989) 497
Chen, Changkang and B.M. Wanklyn, Evaporation kinetics of a halide flux system for the growth of Bi–Sr–Ca–Cu–O superconducting crystals 96 (1989) 547
Chen, H.-C. and Y.-H. Xu, Growth and some properties of undoped and doped $(K_{1-x}Na_x)_{0.4}(Sr_{1-y}Ba_y)_{0.8}Nb_2O_6$ (KNSBN) single crystals with tungsten–bronze structure 96 (1989) 357
Chen, S.L., see Lee 96 (1989) 785
Chen Weidong, Lu Jian, Yu Meifang, Qiao

Yiming and Yuan Shixin, Growth of (111)CdTe on a buffer layer of (100)ZnSe by MBE 96 (1989) 456
Cheng, H.-Y. and E.E. Anderson, The growth of ZnSe single crystals by physical vapor transport 96 (1989) 756
Cheng, V.K.W., E.C.M. Tang and T.B. Tang, The kinetic asymmetry between nucleation growth and dissolution: a Monte Carlo study 96 (1989) 293
Chernov, A.A. and V.S. Dimitrov, Interaction between dislocations and cellular front of crystallization: (0001)SiO_2 face 96 (1989) 304
Chikichev, S.I., see Bosacchi 96 (1989) 899
Chiu, B.S., see Su 96 (1989) 47
Cima, M.J., see Brody 96 (1989) 225
Cockayne, B., see Jones 96 (1989) 769
Colter, P.C., see Lee 96 (1989) 27
Curti, M., see Fornari 96 (1989) 795

Dalas, E. and P.G. Koutsoukos, The effect of magnetic fields on calcium carbonate scale formation 96 (1989) 802
Davey, S.T., M.A.G. Halliwell, D.C. Rogers, M.R. Taylor and E.G. Scott, On the determination of alloy compositions in GaInAs/AlInAs multiple quantum wells 96 (1989) 258
Davies, D.K., see Singh 96 (1989) 969
Davis, S.H., see Merchant 96 (1989) 737
Dazord, J., see Vincent 96 (1989) 871
De Blasi, C., D. Manno, G. Micocci and A. Tepore, Electron diffraction study of In_2Se_3 melt grown crystals 96 (1989) 947
De Cheveigné, S., C. Guthmann, P. Kurowski, E. Vicente and H. Biloni, Directional solidification of metallic alloys: the nature of the bifurcation from planar to cellular interface (E) 96 (1989) 732
Delamore, G.W., see Gibson 96 (1989) 763
Derby, J.J., see Thomas 96 (1989) 135
Dimitrov, V.S., see Chernov 96 (1989) 304
Djuneva, K.D., see Tsukeva 96 (1989) 413
Dobson, P.S., see Nouruzi-Khorasani 96 (1989) 348
Drykin, V.G., see Podolinsky 96 (1989) 445
Duffar, T., see Garandet 96 (1989) 888

Easton, B.C., see Capper 96 (1989) 519
Ehlers, H.L., A.W.R. Leitch and J.S. Vermaak, Scanning photoluminescence study of the spatial uniformity of the growth rates of OMVPE grown GaAs quantum wells 96 (1989) 101
Erman, M., G. Gillardin, J. Le Bris, M. Renaud and E. Tomzig, Characterization of Fe-doped semi-insulating InP by low temperature and room temperature spatially resolved photoluminescence 96 (1989) 469

Farley, C.W., G.J. Sullivan, M.J. Mondry and D.L. Miller, Arsenic flux interruptions: induced RHEED oscillations and measurements of As coverage on the growing (001) MBE GaAs surface 96 (1989) 19
Fatemi, M., A high-resolution double-crystal diffractometer method for the measurement of lattice parameter in single crystals 96 (1989) 316
Favier, J.J., see Garandet 96 (1989) 888
Ferreira, S.O., see Abramof 96 (1989) 637
Firmann, M., see Bilgram 96 (1989) 175
Flemings, M.C., see Brody 96 (1989) 225
Floquet, N., see Bertrand 96 (1989) 708
Flükiger, R., see Wolf 96 (1989) 1010
Fornari, R., J. Kumar, M. Curti and G. Zuccalli, Growth and properties of bulk indium phosphide doubly doped with cadmium and sulphur 96 (1989) 795
Franchi, S., see Bosacchi 96 (1989) 899
Franke, D., see Wolfram 96 (1989) 691
Frigo, D.M., O.F.Z. Khan and P. O'Brien, Growth of epitaxial and highly oriented thin films of cadmium and cadmium zinc sulfide by low-pressure metalorganic chemical vapour deposition using diethyldithiocarbamates 96 (1989) 989
Fu, W.T., see Zandbergen 96 (1989) 716
Fukuda, T., see Shishido 96 (1989) 1

Gabbe, D.R., see Cassanho 96 (1989) 999
Garandet, J.P., On the thermal stresses in vertical gradient freeze furnaces 96 (1989) 680
Garandet, J.P., T. Duffar and J.J. Favier, Vertical gradient freeze growth and characterization of high quality GaSb single crystals 96 (1989) 888
Gardeniers, J.G.E., W.E.J.R. Maas, R.Z.C. van Meerten and L.J. Giling, Influence of temperature on the crystal habit of silicon in the Si–H–Cl CVD system, I. Experimental results 96 (1989) 821
Gardeniers, J.G.E., W.E.J.R. Maas, R.Z.C. van Meerten and L.J. Giling, Influence of temperature on the crystal habit of silicon in the Si–H–Cl CVD system. II. Surface tension of faces in the ⟨110⟩ zones 96 (1989) 832
Gibson, M.A. and G.W. Delamore, Crystal morphologies in iron- and cobalt-based metallic glasses 96 (1989) 763
Giling, L.J., see Visser 96 (1989) 732
Giling, L.J., see Gardeniers 96 (1989) 821
Giling, L.J., see Gardeniers 96 (1989) 832
Gill, W.N., see Tirmizi 96 (1989) 277
Gillardin, G., see Erman 96 (1989) 469
Gireesan, K., see Bhatt 96 (1989) 649
Glicksman, M.E., see Singh 96 (1989) 969

Goldacker, W., see Wolf 96 (1989) 1010
Goodings, C., N.J. Mason, P.J. Walker and D.P. Jebb, A new inlet area design for horizontal MOVPE reactors 96 (1989) 13
Goral, J., see Ruth 96 (1989) 363
Gottlieb, M., see Singh 96 (1989) 969
Govers, C.A.M., see Visser 96 (1989) 732
Grases, F. and P. March, A study about some phosphate derivatives as inhibitors of calcium oxalate crystal growth 96 (1989) 993
Gray, P.A., see Lowry 96 (1989) 774
Gronsky, R., see Lee 96 (1989) 333
Guenais, B., A. Guivarc'h, R. Chaplain, A. Poudoulec and G. Guillot, Evidence for inclusions in rhodium doped molecular beam epitaxy grown GaAs layers 96 (1989) 119
Guillot, G., see Guenais 96 (1989) 119
Guivarc'h, A., see Guenais 96 (1989) 119
Guthmann, C., see De Cheveigné 96 (1989) 732
Gyorgy, E.M., see Brody 96 (1989) 225

Haggerty, J.S., see Brody 96 (1989) 225
Hagino, M., see Zhu 96 (1989) 513
Haldenwang, P., On kinetics and hydrodynamics related to the growth of faceted crystals 96 (1989) 652
Halliwell, M.A.G., see Davey 96 (1989) 258
Han, H.G., see Rao 96 (1989) 807
Hara, K., see Yasuda 96 (1989) 979
Hårsta, A., see Ottosson 96 (1989) 1019
Hartman, P., The effect of surface relaxation on crystal habit: cases of corundum (α-Al_2O_3) and hematite (α-Fe_2O_3) 96 (1989) 667
Hattori, T., see Motojima 96 (1989) 127
Hattori, T., see Motojima 96 (1989) 383
Heinecke, H., see Leiber 96 (1989) 483
Henningsen, T. and N.B. Singh, Crystal characterization by use of birefringence interferometry 96 (1989) 114
Henningsen, T., see Singh 96 (1989) 969
Hicks, T.W. and N. Riley, Boundary layers in magnetic Czochralski crystal growth 96 (1989) 957
Hirata, H. and K. Hoshikawa, Silicon crystal growth in a cusp magnetic field 96 (1989) 747
Holland, L.R., Crucible surface, thermal refraction, boundaries, and interface shape in melt growth 96 (1989) 577
Hoogendoorn, C.J., see Visser 96 (1989) 732
Hoshikawa, K., see Hirata 96 (1989) 747
Hoshino, M., K. Kitahara, K. Kodama and M. Ozeki, GaInP growth by chloride vapor phase epitaxy 96 (1989) 188
Hunt, J.D., see Shangguan 96 (1989) 856
Hürlimann, E., see Bilgram 96 (1989) 175
Hwang, D.L., Y.S. Tsai, H.L. Hwang and C.Y. Sun, Liquid-phase epitaxial growth of mercury cadmium telluride for fiber optic communication photodetectors 96 (1989) 673
Hwang, H.L., see Hwang 96 (1989) 673

Iijima, M. and Y. Moriwaki, Effects of inorganic ions on morphology of octacalcium phosphate grown on cation selective membrane at physiological temperature and pH in relation to enamel formation 96 (1989) 59
Inada, T., Y. Otoki, K. Ohata, S. Taharasako and S. Kuma, Effects of thermal history during LEC growth on behavior of excess arsenic in semi-insulating GaAs 96 (1989) 327
Ivanov, S.V., see Kop'ev 96 (1989) 533
Iwanaga, H., see Motojima 96 (1989) 127
Iwanaga, H., see Motojima 96 (1989) 383

Jacobs, P.R., see Jones 96 (1989) 769
Jacquot, D., see Bertrand 96 (1989) 708
Jaeger, H., M. Aslan, K. Schulze and G. Petzow, Processing and superconducting properties of Bi–Sr–Ca–Cu–O compounds 96 (1989) 459
Jebb, D.P., see Goodings 96 (1989) 13
Jenssen, H.P., see Cassanho 96 (1989) 999
Jin, J.-M. and N.-B. Ming, A comparison between the growth mechanism of stacking fault and of screw dislocation 96 (1989) 442
Johnson, D.W., see Brody 96 (1989) 225
Jones, A.C., P.R. Jacobs, S. Rushworth, J.S. Roberts, C. Button, P.J. Wright, P.E. Oliver and B. Cockayne, Growth of $Al_xGa_{1-x}As$ by MOVPE using a new alkylaluminium precursor 96 (1989) 769
Jones, E.D. and N.M. Stewart, Self-diffusion of cadmium into the ternary compound indium cadmium sulphide ($In_{0.67x}Cd_{1-x}S$) 96 (1989) 40
Jones, E.D., N.M. Stewart and V. Thambipillai, Self-diffusion of cadmium into cadmium sulphide 96 (1989) 453
Jones, I.P., see Nouruzi-Khorasani 96 (1989) 348
Jürgensen, H., see Westphalen 96 (1989) 982

Kadowaki, K., see Menken 96 (1989) 1002
Kania, A., Flux growth of $AgTa_xNb_{1-x}O_3$ (ATN) solid solution single crystals 96 (1989) 703
Kanter, Yu.O., see Bosacchi 96 (1989) 899
Kashchiev, D., see Obretenov 96 (1989) 843
Kerr, O.S. and A.A. Wheeler, The effect of a magnetic field on the flux of a contaminant dissolving into the crucible wall boundary layer in Czochralski crystal growth 96 (1989) 915
Khan, O.F.Z., see Frigo 96 (1989) 989
Kim, Do Hyun and R.A. Brown, Models for convection and segregation in the growth of HgCdTe by the vertical Bridgman method 96 (1989) 609

Kim, M.H., see Lee 96 (1989) 27
Kimura, M., see Sukegawa 96 (1989) 584
Kinoshita, K. and T. Yamada, Surface tension of $Pb_{0.8}Sn_{0.2}Te$ melt and the effect of Marangoni convection in microgravity crystal growth 96 (1989) 953
Kitagawara, Y., see Kuwabara 96 (1989) 572
Kitahara, K., see Hoshino 96 (1989) 188
Kitamura, M., Polymorphism in the crystallization of L-glutamic acid 96 (1989) 541
Kleijn, C.R., see Visser 96 (1989) 732
Kodama, K., see Hoshino 96 (1989) 188
Koizumi, Y., see Kuroda 96 (1989) 7
Kojima, H., see Tanaka 96 (1989) 711
Kondo, N., see Yamamoto 96 (1989) 705
Kop'ev, P.S., S.V. Ivanov, A.Yu. Yegorov and D.Yu. Uglov, Influence of growth parameters and conditions on the oval defect density in GaAs layers grown by MBE 96 (1989) 533
Kordoš, P., see Novák 96 (1989) 645
Koutsoukos, P.G., see Dalas 96 (1989) 802
Koyama, T., K. Yamashita and K. Kumata, Etch pit study of ZnSe single crystal grown by the iodine transport method 96 (1989) 217
Kukimoto, H., see Yasuda 96 (1989) 979
Kuliffayová, M., see Novák 96 (1989) 645
Kuma, S., see Inada 96 (1989) 327
Kumar, J., see Fornari 96 (1989) 795
Kumata, K., see Koyama 96 (1989) 217
Kuroda, N., S. Sugou, Y. Koizumi and T. Uji, Epitaxial growth of highly Fe-doped semi-insulating InP layers by N_2 carrier gas mixed hydride vapor phase epitaxy 96 (1989) 7
Kurowski, P., see De Cheveigné 96 (1989) 732
Kuwabara, S., Y. Kitagawara, N. Noto, S. Nagasawa and T. Takenaka, Observation of microdefects in indium-doped GaAs crystals by preferential etching and infrared light scattering tomography 96 (1989) 572

Lahtinen, J.A., see Tuomi 96 (1989) 881
Larsen, C.A., see Li 96 (1989) 906
Laudise, R.A., see Brody 96 (1989) 225
Le Bris, J., see Erman 96 (1989) 469
Lee, B., S.S. Bose, M.H. Kim, A.D. Reed, G.E. Stillman, W.I. Wang, L. Vina and P.C. Colter, Orientation dependent amphoteric behavior of Group IV impurities in the molecular beam epitaxial and vapor phase epitaxial growth of GaAs 96 (1989) 27
Lee, B.-T., R. Gronsky and E.D. Bourret, Transmission electron microscope study of arsenic precipitates in GaAs: morphology and orientation relationship with the matrix 96 (1989) 333
Lee, C.T., Y.K. Su and S.L. Chen, Dependence of ZnO films on sputtering parameters and SAW device on ZnO/InP 96 (1989) 785
Leiber, J., A. Brauers, H. Heinecke, H. Lüth and P. Balk, Growth of GaAs and InP on Si using plasma stimulated MOCVD 96 (1989) 483
Leitch, A.W.R., see Ehlers 96 (1989) 101
Li, S.H., N.I. Buchan, C.A. Larsen and G.B. Stringfellow, OMVPE growth mechanism for GaP using tertiarybutylphosphine and trimethylgallium 96 (1989) 906
Lideikis, T. and G. Treideris, Photoluminescence study of acceptors in silicon-doped gallium arsenide grown by metalorganic chemical vapor deposition 96 (1989) 790
Lipsanen, H., see Tuomi 96 (1989) 881
Logan, R.A., see Tuomi 96 (1989) 881
Lowry, S.A., M.H. McCay, T.D. McCay and P.A. Gray, Surface tension measurements of aqueous ammonium chloride (NH_4Cl) in air 96 (1989) 774
Lu Jian, see Chen Weidong 96 (1989) 456
Lüth, H., see Leiber 96 (1989) 483
Lyons, M.H., Factors influencing the presence and detection of compositional grading at semiconductor hetero-epitaxial interfaces 96 (1989) 339

Maas, W.E.J.R., see Gardeniers 96 (1989) 821
Maas, W.E.J.R., see Gardeniers 96 (1989) 832
Manno, D., see De Blasi 96 (1989) 947
March, P., see Grases 96 (1989) 993
Mason, N.J., see Goodings 96 (1989) 13
Matsuoka, M. and R. Ozawa, Determination of solid–liquid phase equilibria of binary organic systems by differential scanning calorimetry 96 (1989) 596
Maxey, C.D., see Capper 96 (1989) 519
Mazelsky, R., see Singh 96 (1989) 969
McAllister, T., Chemical kinetics of telluride pyrolysis 96 (1989) 552
McCay, M.H., see Lowry 96 (1989) 774
McCay, T.D., see Lowry 96 (1989) 774
Menken, M.J.V., K. Kadowaki and A.A. Menovsky, Single crystal growth of the high-T_c superconductors $REBa_2Cu_3O_{7-x}$ (RE = Y, Er) 96 (1989) 1002
Menovsky, A.A., see Menken 96 (1989) 1002
Merchant, G.J. and S.H. Davis, Flow-induced morphological instabilities due to temporally-modulated stagnation-point flow 96 (1989) 737
Mercier, J., see Regolini 96 (1989) 505
Micocci, G., see De Blasi 96 (1989) 947
Middleman, S., see Quinn 96 (1989) 589
Miller, D.L., see Farley 96 (1989) 19
Ming, N.-B., see Jin 96 (1989) 442

Miyao, M., see Zhu 96 (1989) 513
Mizuta, M., see Yasuda 96 (1989) 979
Monberg, E., see Tuomi 96 (1989) 881
Mondry, M.J., see Farley 96 (1989) 19
Morvic, M., see Novák 96 (1989) 645
Motai, K., see Shishido 96 (1989) 1
Motakef, S., Thermoelastic analysis of GaAs in LEC growth configuration. III. Thermal conditions for control of stresses in low pressure systems 96 (1989) 201
Motakef, S., see Cazin-Bourguignon 96 (1989) 390
Motakef, S., see Bordui 96 (1989) 405
Motojima, S., C. Ohashi, T. Hattori and H. Iwanaga, Single crystal growth of Cr_3Si and Cr_5Si_3 using in-situ CVD process 96 (1989) 127
Motojima, S., S. Ueno, T. Hattori and H. Iwanaga, Preparation of whiskers and spring-like fibres of Si_3N_4 by impurity-activated chemical vapour deposition 96 (1989) 383
Moriwaki, Y., see Iijima 96 (1989) 59

Nagasawa, S., see Kuwabara 96 (1989) 572
Nakada, I. and E. Bauser, Microstep structures on prismatic faces of vapour grown $NbSe_4I_{0.33}$ crystals 96 (1989) 234
Nakada, I. and E. Bauser, Origin of multiple steps in vapour growth of $NbSe_4I_{0.33}$ 96 (1989) 243
Nanishi, Y., see Yamamoto 96 (1989) 705
Nishio, J. and K. Terashima, Influence of melt preparation on residual impurity concentration in semi-insulating LEC GaAs 96 (1989) 605
Nomura, T., see Zhu 96 (1989) 513
Noto, N., see Kuwabara 96 (1989) 572
Noufi, R., see Ruth 96 (1989) 363
Nouruzi-Khorasani, A., I.P. Jones, P.S. Dobson, D.J. Williams and M.G. Astles, Transmission electron microscopy of LPE grown CdHgTe 96 (1989) 348
Novák, J., M. Kuliffayová, M. Morvic and P. Kordoš, Growth and properties of low-doped $In_{0.53}Ga_{0.47}As$ LPE layers using rare-earth oxides 96 (1989) 645

O'Brien, P., see Frigo 96 (1989) 989
Obretenov, W., D. Kashchiev and V. Bostanov, Unified description of the rate of nucleation-mediated crystal growth 96 (1989) 843
Obst, B., see Wolf 96 (1989) 1010
Ogawa, T., A study on dislocation lines in an In-doped LEC GaAs crystal by IR light scattering and transmission microscopy 96 (1989) 777
Ohashi, C., see Motojima 96 (1989) 127
Ohata, K., see Inada 96 (1989) 327
Ohsaka, K. and E.H. Trinh, Melting and solidification of acoustically levitated drops 96 (1989) 973
Oliver, P.E., see Jones 96 (1989) 769
Ota, T., see Yokoyama 96 (1989) 490
Otoki, Y., see Inada 96 (1989) 327
Ottosson, M., A. Hårsta and J.-O. Carlsson, Thermodynamic investigation of CVD of the superconducting $YBa_2Cu_3O_{7-x}$ phase using halide precursors 96 (1989) 1019
Ozawa, R., see Matsuoka 96 (1989) 596
Ozeki, M., see Hoshino 96 (1989) 188

Pałosz, W., see Wiedemeier 96 (1989) 933
Pandya, G.R., see Bhatt 96 (1989) 649
Partanen, J., see Tuomi 96 (1989) 881
Paszkowicz, W., see Strupiński 96 (1989) 107
Patnaik, S., R.A. Brown and C.A. Wang, Hydrodynamic dispersion in rotating-disk OMVPE reactors: numerical simulation and experimental measurements 96 (1989) 153
Peneva, S.K., see Tsukeva 96 (1989) 413
Petzow, G., see Jaeger 96 (1989) 459
Pickenhain, R., see Schwetlick 96 (1989) 378
Piña, C., P. Bosch, D. Acosta, J. Barreto, A. Vazquez and E. Camarillo, Growth of MoS_2 and MoS_2 : Co crystals using I_2 as transport material 96 (1989) 685
Podolinsky, V.V., Yu.N. Taran and V.G. Drykin, Classification of binary eutectics 96 (1989) 445
Porte, L., see Vincent 96 (1989) 871
Poudoulec, A., see Guenais 96 (1989) 119

Qiao Yiming, see Chen Weidong 96 (1989) 456
Quinn, K. and S. Middleman, Continuous filament coating by chemical vapor deposition. I. The well mixed reactor 96 (1989) 589

Ranganathan, S., see Swamy 96 (1989) 628
Ranta-Aho, T., see Tuomi 96 (1989) 881
Rao, Y.K. and H.G. Han, Mass transfer and surface reaction in the growth and etching of GaAs(s) 96 (1989) 807
Ray, S.K. and S. Utku, Effects of viscosity on the continuous growth of dendritic silicon crystal ribbon 96 (1989) 561
Reed, A.D., see Lee 96 (1989) 27
Regolini, J.L., D. Bensahel, J. Mercier and E. Scheid, Silicon selective epitaxial growth at reduced pressure and temperature 96 (1989) 505
Reier, F.W., see Wolfram 96 (1989) 691
Reihlen, E.H., see Chen 96 (1989) 497
Renaud, M., see Erman 96 (1989) 469
Rhodes, W.W., see Brody 96 (1989) 225
Riley, N., see Hicks 96 (1989) 957
Roberts, J.S., see Jones 96 (1989) 769
Rogers, D.C., see Davey 96 (1989) 258
Roth, G., see Wolf 96 (1989) 1010
Rushworth, S., see Jones 96 (1989) 769
Ruth, M., J. Tuttle, J. Goral and R. Noufi,

Aluminum doped zinc oxide thin films deposited by ion beam sputtering 96 (1989) 363

Sasaki, T., see Shishido 96 (1989) 1
Scheel, H.J., see Boutellier 96 (1989) 465
Scheid, E., see Regolini 96 (1989) 505
Schmid, H., see Boutellier 96 (1989) 465
Schulze, K., see Jaeger 96 (1989) 459
Schumann, H., see Wolfram 96 (1989) 691
Schwabe, R., see Schwetlick 96 (1989) 378
Schwetlick, S., W. Seifert, R. Pickenhain and R. Schwabe, Reduced EL2 concentration in MOCVD GaAs by addition of NH_3 during growth 96 (1989) 378
Scott, E.G., see Davey 96 (1989) 258
Seifert, W., see Schwetlick 96 (1989) 378
Sekerka, R.F., see Brush 96 (1989) 419
Sevov, S.H., see Tsukeva 96 (1989) 413
Shang Shuxia, see Wang Hong 96 (1989) 221
Shangguan, D.K. and J.D. Hunt, Dynamical study of the pattern formation of faceted cellular array growth 96 (1989) 856
Shen Xiaonong, see Wang Hong 96 (1989) 221
Shishido, T., K. Ukei, N. Toyota, T. Sasaki, Y. Watanabe, K. Motai, T. Fukuda, H. Takeya and H. Takei, Flux growth of a new ternary superconducting crystal Nb_5Sn_2Ga 96 (1989) 1
Shu Guangji, see Wang Nan 96 (1989) 996
Singh, N.B., see Henningsen 96 (1989) 114
Singh, N.B., D.K. Davies, M. Gottlieb, T. Henningsen, R. Mazelsky and M.E. Glicksman, Effect of temperature gradient on the optical quality of mercurous chloride crystals 96 (1989) 969
Song, S.A. and D.J. Barber, Can the molecular staggering angle be determined from a single diffraction pattern? 96 (1989) 985
Stewart, N.M., see Jones 96 (1989) 40
Stewart, N.M., see Jones 96 (1989) 453
Stillman, G.E., see Lee 96 (1989) 27
Stringfellow, G.B., see Chen 96 (1989) 497
Stringfellow, G.B., see Li 96 (1989) 906
Strupiński, W., J. Bąk-Misiuk, W. Paszkowicz and W. Wierzchowski, X-ray investigations of GaP:N,S epitaxial layers applied in light emitting diodes 96 (1989) 107
Su, Y.K., M.C. Wu and B.S. Chiu, The effect of lattice mismatch on the properties of $In_{1-x}Ga_xAs/InP$ heterojunctions 96 (1989) 47
Su, Y.K., see Wu 96 (1989) 52
Su, Y.K., see Lee 96 (1989) 785
Sugou, S., see Kuroda 96 (1989) 7
Sukegawa, T., M. Kimura and A. Tanaka, Compensation effect of lattice constant in silicon n^+–n^- junctions by liquid phase epitaxy 96 (1989) 584
Sullivan, G.J., see Farley 96 (1989) 19
Sun, B.N. and A. Baronnet, Hydrothermal growth of OH-phlogopite single cyrstals. I. Undoped growth medium 96 (1989) 265
Sun, B.N., see Boutellier 96 (1989) 465
Sun, C.Y., see Hwang 96 (1989) 673
Sunder, W.A., see Brody 96 (1989) 225
Swamy, V.T., S. Ranganathan and K. Chattopadhyay, On the resolidification behaviour of microsecond pulsed-laser-melted pool of bismuth 96 (1989) 628

Taharasako, S., see Inada 96 (1989) 327
Tai, C.Y. and K.H. Yu, Growth kinetics of potassium alum crystal in a well-agitated vessel 96 (1989) 849
Takahashi, J., see Yokoyama 96 (1989) 490
Takei, H., see Shishido 96 (1989) 1
Takenaka, T., see Kuwabara 96 (1989) 572
Takeya, H., see Shishido 96 (1989) 1
Tanaka, A., see Sukegawa 96 (1989) 584
Tanaka, I., K. Yamane and H. Kojima, Single crystal growth of superconducting $La_{2-x}Sr_xCuO_4$ by the TSFZ method 96 (1989) 711
Tang, E.C.M., see Cheng 96 (1989) 293
Tang, T.B., see Cheng 96 (1989) 293
Taran, Yu.N., see Podolinsky 96 (1989) 445
Taylor, M.R., see Davey 96 (1989) 258
Tellier, C.R., A three-dimensional kinematic model for the dissolution of crystals 96 (1989) 450
Tepore, A., see De Blasi 96 (1989) 947
Terashima, K., see Nishio 96 (1989) 605
Thambipillai, V., see Jones 96 (1989) 453
Thomas, P.D., J.J. Derby, L.J. Atherton, R.A. Brown and M.J. Wargo, Dynamics of liquid-encapsulated Czochralski growth of gallium arsenide: comparing model with experiment 96 (1989) 135
Tirmizi, S.H. and W.N. Gill, Experimental investigation of the dynamics of spontaneous pattern formation during dendritic ice crystal growth 96 (1989) 277
Tomzig, E., see Erman 96 (1989) 469
Toyota, N., see Shishido 96 (1989) 1
Treideris, G., see Lideikis 96 (1989) 790
Trinh, E.H., see Ohsaka 96 (1989) 973
Tsai, Y.S., see Hwang 96 (1989) 673
Tsukeva, E.A., K.D. Djuneva, S.K. Peneva and S.H. Sevov, RHEED study of thin tin films grown at deposition rates of 2 to 10 Å/s 96 (1989) 413
Tuomi, T., H. Lipsanen, T. Ranta-Aho, J. Partanen, J.A. Lahtinen, E. Monberg and R.A. Logan, Synchrotron section topographic study of defects in InP substrates and quaternary laser structures 96 (1989) 881
Tuttle, J., see Ruth 96 (1989) 363

Uchida, N., see Yamamoto 96 (1989) 369
Ueno, S., see Motojima 96 (1989) 383
Uglov, D.Yu., see Kop'ev 96 (1989) 533
Uji, T., see Kuroda 96 (1989) 7
Ukei, K., see Shishido 96 (1989) 1
Utku, S., see Ray 96 (1989) 561

Van Meerten, R.Z.C., see Gardeniers 96 (1989) 821
Van Meerten, R.Z.C., see Gardeniers 96 (1989) 832
Van Tendeloo, G., see Zandbergen 96 (1989) 716
Vazquez, A., see Piña 96 (1989) 685
Vermaak, J.S., see Ehlers 96 (1989) 101
Vicente, E., see De Cheveigné 96 (1989) 732
Vina, L., see Lee 96 (1989) 27
Vincent, C., J. Dazord, H. Vincent, J. Bouix et L. Porte, Effet des conditions expérimentales sur la CVD réactive de couches minces de TiC sur carbone 96 (1989) 871
Vincent, H., see Vincent 96 (1989) 871
Visser, E.P., C.R. Kleijn, C.A.M. Govers, C.J. Hoogendoorn and L.J. Giling, Return flows in horizontal MOCVD reactors studied with the use of TiO_2 particle injection and numerical calculation (E) 96 (1989) 732

Walker, P.J., see Goodings 96 (1989) 13
Wang, C.A., see Patnaik 96 (1989) 153
Wang Hong, Shang Shuxia, Wang Zhuo and Shen Xiaonong, Crystal growth of the new superconducting compound $Pb_{0.6}Bi_3Sr_2CaCu_3O_x$ by the flux method 96 (1989) 221
Wang Nan and Shu Guangji, Merging growth of metallic crystal in shear flow 96 (1989) 996
Wang, W.I., see Lee 96 (1989) 27
Wang Zhuo, see Wang Hong 96 (1989) 221
Wanklyn, B.M., see Chen 96 (1989) 547
Wargo, M.J., see Thomas 96 (1989) 135
Watanabe, Y., see Shishido 96 (1989) 1
Westphalen, R., H. Jürgensen and P. Balk, Epilayers with extremely low dislocation densities grown by isoelectronic doping of hydride VPE grown InP 96 (1989) 982
Wheeler, A.A., see Kerr 96 (1989) 915
Whiffin, P.A.C., see Capper 96 (1989) 519
Wiedemeier, H. and W. Pałosz, Mass flux and crystal composition in the $Hg_{0.8}Cd_{0.2}Te$–HgI_2 vapor transport system 96 (1989) 933
Wierzchowski, W., see Strupiński 96 (1989) 107
Williams, D.J., see Nouruzi-Khorasani 96 (1989) 348
Wolf, Th., W. Goldacker, B. Obst, G. Roth and R. Flükiger, Growth of thick $YBa_2Cu_3O_{7-x}$ single crystals from Al_2O_3 crucibles 96 (1989) 1010
Wolfram, P., F.W. Reier, D. Franke and H. Schumann, Very high purity InP layers grown by adduct-MOVPE 96 (1989) 691
Wright, P.J., see Jones 96 (1989) 769
Wu, F.C. and S.C. Yu, The crystallization and phase transformation of stabilizer-doped zirconia powders with H_2SO_4 additive 96 (1989) 96
Wu, M.C., see Su 96 (1989) 47
Wu, M.C. and Y.K. Su, Liquid-phase epitaxial growth of $Al_xGa_{1-x}As$ with $0 \leq x \leq 0.85$ 96 (1989) 52

Xu, Y.-H., see Chen 96 (1989) 357

Yamada, T., see Kinoshita 96 (1989) 953
Yamaguchi, M., see Yamamoto 96 (1989) 369
Yamai, I., see Yokoyama 96 (1989) 490
Yamamoto, A., N. Uchida and M. Yamaguchi, Optimization of InP/Si heteroepitaxial growth conditions using organometallic vapor phase epitaxy 96 (1989) 369
Yamamoto, N., N. Kondo and Y. Nanishi, Selective area growth of GaAs by electron-cyclotron resonance plasma-excited molecular-beam epitaxy (ECR-MBE) 96 (1989) 705
Yamane, K., see Tanaka 96 (1989) 711
Yamashita, K., see Koyama 96 (1989) 217
Yasuda, T., K. Hara, M. Mizuta and H. Kukimoto, Plasma-enhanced doping of manganese in zinc sulfide layers during metalorganic chemical vapor deposition 96 (1989) 979
Yegorov, A.Yu, see Kop'ev 96 (1989) 533
Yokoyama, M., T. Ota, I. Yamai and J. Takahashi, Flux growth of perovskite-type $La_{2/3}TiO_{3-x}$ crystals 96 (1989) 490
Young, G.W. and A. Chait, Steady-state thermal-solutal diffusion in a float zone 96 (1989) 65
Yu, K.H., see Tai 96 (1989) 849
Yu Meifang, see Chen Weidong 96 (1989) 456
Yu, S.C., see Wu 96 (1989) 96
Yuan Shixin, see Chen Weidong 96 (1989) 456

Zandbergen, H.W., W.T. Fu, G. Van Tendeloo and S. Amelinckx, Electron microscopy on superconducting $(Pb, Bi)_2Sr_{2-x}La_xCu_2O_{6+\delta}$ 96 (1989) 716
Zhu, Z., T. Nomura, M. Miyao and M. Hagino, MBE growth mechanism of ZnSe: growth rate and surface coverage 96 (1989) 513
Zuccalli, G., see Fornari 96 (1989) 795

Journal of Crystal Growth 96 (1989) 1043–1046
North-Holland, Amsterdam

SUBJECT INDEX

Acousto-optic devices 785
Adduct 378, 691
Adsorption 19, 667, 821, 832, 993
Alloys 735, 763, 996
Alum
– potassium 849
Aluminum
– alloys 735
– gallium arsenide 19, 52, 732, 769
– organic 769
– oxide 667
– zinc alloy 996
Ammonium
– chloride 774
Apparatus
– for dentritic growth
– – of ice 277
– – of krypton 175
– – of xenon 175
– for melt growth
– – by Bridgman–Stockbarger method
– – – of mercury cadmium telluride 609
– – by Czochralski method
– – – of gallium arsenide 390
– – – of potassium sodium strontium barium niobate 357
– – – of silicon 747
– – by floating zone
– – – of bismuth calcium strontium cuprate 225
– – by vertical gradient freeze
– – – of gallium antimonide 888
– for solution growth
– – by flux method
– – – of pentaniobium ditin gallium 1
– – – of yttrium barium cuprate 465
– – by hydrothermal growth
– – – of mica 265
– – by low temperature method
– – – at constant supersaturation
– – – – of calcium carbonate 802
– for thin film growth
– – by ion beam sputtering
– – – of zinc oxide 363
– – by vapor phase epitaxy
– – – through chemical vapor deposition
– – – – of gallium indium phosphide 188
– – – – of titanium carbide 871
– – – through metalorganic chemical vapor deposition
– – – – of gallium arsenide 101
– – – – of III–V compounds 13
– for whiskers and fiber growth
– – of silicon nitride 383
– for miscellaneous purposes
– – double crystal diffractometry 316
– – evaluation of optical quality by interferometry 114
– – scanning photoluminescence 469
– – testing of model cell/liner using smoke 13
Arsenic
– organic 497

Bismuth 628
– calcium strontium cuprate 225, 459, 547
Boundary layer control 65, 577, 652, 915, 957

Cadmium
– mercury telluride 348, 519, 552, 577, 609, 673, 933
– organic 989
– sulphide 453, 989
– telluride 456
– zinc sulphide 989
Calcium
– apatite 59
– carbonate 802
– (octa) phosphate 59
– oxalate monohydrate 993
Cellular growth 304, 737, 856
Characterization methods
– by absorption spectroscopy 357, 363
– by Auger electron spectroscoy 383
– by deep level transient spectroscopy 378
– by differential scanning calorimetry 596
– by differential thermal analysis 96, 459
– by electrical methods 1, 7, 27, 47, 52, 188, 221, 225, 327, 363, 378, 459, 490, 497, 519, 637, 645, 649, 711, 790, 795, 888, 982
– by electrolyte electroreflectance spectroscopy 47
– by electron microscopy 1, 47, 59, 119, 127, 188, 217, 221, 258, 265, 333, 339, 348, 357, 369, 383, 445, 459, 483, 490, 533, 572, 628, 685, 691, 705, 708, 711, 716, 756, 763, 785, 871, 947, 985, 989
– by electron spectroscopy for chemical analysis 871
– by ferroelectricity 357
– by Fourier transform infrared 673
– by inductively coupled plasma spectrometry 1
– by interferometry 114
– by light scattering tomography 572
– by magnetic properties 1, 221, 1002
– by Mössbauer spectroscopy 413
– by nuclear magnetic resonance 769
– by optical microscopy 47, 225, 234, 243, 265, 277, 304, 357, 405, 459, 490, 497, 519, 541, 628, 637, 673, 703, 708, 756, 763, 777

– by optical properties 969
– by photoluminescence 27, 47, 52, 101, 107, 119, 188, 258, 339, 369, 378, 469, 483, 497, 673, 691, 769, 790
– by photothermal ionization spectroscopy 27
– by radiotracer 453
– by Raman spectroscopy 47, 258
– by reflection high energy electron diffraction 19, 369, 413, 456, 513, 533, 708, 899, 989
– by scattering of centers 327
– by secondary ion mass spectrometry 7, 119, 217, 378
– by surface tension 774
– by synchrotron topography 881
– by thermogravimetry 96
– by X-ray photoelectron spectroscopy 871
– by X-ray techniques, 1, 47, 52, 96, 107, 127, 217, 221, 225, 258, 316, 339, 357, 363, 369, 383, 413, 456, 459, 483, 490, 519, 541, 584, 628, 637, 673, 685, 703, 708, 711, 785, 871, 982, 999
Chromium
– silicides 127
Cobalt
– silicide boride alloys 763
Computer simulation 552, 561
Consitutional supercooling 735
Convection 65, 277, 405, 609, 652, 915, 953

Dendritic growth 175, 277, 419, 561, 774, 973
Devices 107, 369
Diffusional control 40, 65, 453, 897
Dislocations 47, 107, 201, 217, 234, 243, 304, 333, 348, 390, 442, 469, 561, 649, 673, 680, 756, 777, 795, 856, 881, 888, 982
Dissolution 293, 450
Distribution coefficient 795
Dopants 7, 96, 107, 119, 188, 217, 316, 469, 584, 790, 795, 982

Erbium
– barium cuprate 1002
Etching
– chemical 27, 217, 357, 369, 378, 413, 450, 490, 572, 649, 756, 785, 795, 807, 888
– photoelectrochemical 369
Eutectic growth 445

Facet growth 821, 832
Fiber growth
– of silicon nitride 383
Fiber optics 673
Finite element analysis 135, 153

Gadolinium
– barium cuprate 1002
Gallium
– antimonide 13, 888
– arsenide 13, 19, 27, 101, 119, 135, 153, 201, 316, 327, 333, 378, 390, 483, 497, 533, 572, 605, 693, 705, 732, 777, 790, 807, 899
– indium arsenide 258, 339
– indium phosphide 188
– organic 378, 497, 693, 906
– phosphide 107, 906
Germanium
– gallium 65
Glasses 763
Glutamic acid, L 541
Grain boundary 304, 628, 996

Heat flow control 65, 101, 135, 201, 277, 390, 419, 577, 888
Heterojunction 47, 52, 153, 732
Hydrodynamics 405, 609, 652

Ice 277
Impurity 7, 27, 52, 383, 605, 645, 652, 769, 790, 979
Inclusions 405
Indium
– arsenide 13
– cadmium sulphide 40
– gallium arsenide 47, 645
– organic 369, 691
– phosphide 7, 339, 369, 469, 483, 691, 795, 881, 982
– selenide 947
Interface 65, 135, 175, 188, 201, 277, 333, 339, 348, 390, 445, 561, 577, 652, 732, 744, 856, 957, 996
Iron
– oxide 667
– silicide boride alloys 763

Kinetics
– of evaporation 547
– of etching reaction 807
– of growth 7, 27, 52, 101, 175, 225, 265, 277, 293, 304, 378, 383, 413, 419, 442, 459, 505, 513, 561, 589, 652, 705, 756, 802, 807, 843, 849, 871, 993
– of interface control 47, 577, 807
– of nucleation 293, 541, 843
– of pattern formation 277
– of pyrolysis 552
Krypton 175

Lanthanide
– diphthalocyanides 985
Lanthanum
– strontium cuprate 711
– titanate 490
Lattice mismatch 47, 107, 188, 258, 339, 584, 673, 735, 881, 982
Lead
– alloys 735
– bismuth strontium calcium cuprate 221
– strontium lanthanum cuprate 716
– tin telluride 637, 953
Light emitting diodes 107

Mathematical model 65, 419, 732
Melt growth technique
– by Bridgman–Stockbarger method

– – of gallium antimonide 888
– – of gallium arsenide 333
– – of indium selenide 947
– – of mercury cadmium telluride 577, 609
– – of III–V compounds 680
– – of tin diselenide 649
– – of tin selenide 649
– by containerless processing
– – of succinonitrile 973
– by Czochralski method
– – of gallium arsenide 135, 201, 327, 333, 390, 572, 605, 777
– – of indium phosphide 469, 795, 881
– – of potassium sodium strontium barium niobate 357
– – of silicon 747
– – theory of 915, 957
– by floating zone method
– – of bismuth calcium strontium cuprate 225
– – of lanthanum strontium cuprate 711
– – theory of 67
– by laser melting
– – of bismuth 628
– by planar flow casting method
– – of alloys 763
– by uniaxial solidification
– – of indium phosphide 881
– – of lead tin telluride 953
– – of mercury cadmium telluride 577
– – of III–V compounds 680
– theory of 577
Mercury
– cadmium telluride 348, 519, 552, 577, 609, 673, 933
– (I) chloride 969
Mica 265
Microgravity 65, 577, 609, 953
Molybdenum
– disulphide 685
– oxides 708
Monte Carlo method 293, 442, 843
Morphology stability 419, 445, 652, 735, 737
Morphology of growth 1, 59, 127, 135, 175, 188, 201, 225, 234, 243, 265, 277, 304, 333, 357, 369, 383, 390, 419, 445, 483, 490, 533, 541, 637, 652, 667, 708, 763, 785, 821, 832, 871, 996, 1010

Neodymium
– cerium cuprate 999
– cuprate 999
Niobium
– (penta) ditin gallium 1
– selenide iodide 234, 243
Nucleation 293, 327, 333, 369, 541, 577, 628, 637, 756, 843, 856
Numbers
– Biot 65
– Ekman 732
– Grashof 153
– Lewis 65
– Peclet 65, 153, 175, 609
– Prandtl 65, 732
– Rayleigh 609, 732
– Reynolds 732
– Schmidt 65, 609, 849
– Stefan 65, 609

Organic crystals 445, 541, 596, 735, 973, 985, 993

Perfection of crystals 40, 107, 243, 304, 333, 357, 378, 405, 469, 572, 680, 716, 777, 888, 982
Periodic bond chain theory 27, 821, 832
Phase diagrams 596, 716, 774, 899, 1010, 1019
Phenomenological theory 735
Phosphorus
– organic 691, 906
Polymorphism/polytypism 541
Potassium
– alum
– sodium strontium barium niobate 357
– titanyl phosphate 405
Precursor 769

Quantum wells/size effects 101, 258, 369
Quartz 304

Radiation 65
Radiotracer 40

SAW devices 785
Segregation 609, 795
Silicates 265
Silicon 65, 505, 561, 584, 589, 747, 821, 832
– dioxide 304
– nitride 383
Silver
– tantalate niobate 703
Solar cells 369
Solid solution 703
Solution growth technique
– by flux method
– – of bismuth calcium strontium cuprate 547
– – of lanthanum titanate 490
– – of lead bismuth strontium calcium cuprate 221
– – of pentaniobium ditin gallium 1
– – of potassium titanyl phosphate 405
– – of rare earth barium cuprates 1002
– – of silver tantalate niobate 703
– – of yttrium barium aluminate 1010
– – of yttrium barium cuprate 1010
– by hydrothermal method
– – of mica 265
– by low temperature method
– – of calcium carbonate 802
– – of calcium (octa) phosphate 59
– – of glutamic acid, L 541
– – of potassium alum 849
– – of zirconia 96

– by partial melting
– – of erbium barium cuprate 1002
– – of gadolinium bariuum cuprate 1002
– – of yttrium barium cuprate 1002
Stefan problem of moving boundary problem 65, 135, 390, 419, 609, 807
Step 234, 243, 652, 832
Strain 201, 333, 390, 561, 584, 680
Succinonitrile 973
Superconductivity 1, 221, 225, 459, 465, 711, 716, 1002, 1010, 1019
– bulk 1, 221, 225, 459, 465, 711, 716, 1002, 1010
– characterization 1, 221, 225, 459, 711, 1002, 1010
– crystal chemistrry 1, 221, 225, 459, 711, 716, 1002, 1010, 1019
– high T_c 221, 225, 459, 465, 711, 716, 1002, 1010, 1019
– low T_c 1
– phase relationships 716, 1010, 1019
– stoichiometry 1, 221, 225, 459, 711, 716
– thin films 1019
Supercooling, supersaturation 52, 175, 265, 405, 442, 541, 802
Superlattices 339, 413
Surface energy, determination of 667, 832, 953
Surface processes, theory 175, 378, 450
Surface structure 19, 188, 234, 369, 413, 445, 519

Tellurium
– organic 552
Thermodynamics 505, 533, 693, 933, 1019
Thin film growth
– by hot wall epitaxy
– – of lead tin telluride 637
– by ion beam sputtering
– – of zinc oxide 363
– by liquid phase epitaxy
– – of aluminum gallium arsenide 52
– – of indium gallium arsenide 47, 645
– – of mercury cadmium telluride 348, 673
– – of silicon 584
– by molecular beam epitaxy
– – of cadmium telluride 456
– – of gallium arsenide 19, 27, 119, 533, 705, 899
– – of gallium indium arsenide 258
– – of zinc selenide 513
– – theory of 899
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of gallium arsenide 27, 153, 803
– – – of gallium indium phosphide 188
– – – of gallium phosphide 107
– – – of indium phosphide 7, 982
– – – of silicon 505, 589, 821, 832
– – – of titanium carbide 871
– – – of yttrium barium cuprate 1019
– – – of zinc sulphide 979
– – – theory of 153
– – through evaporation and condensation
– – – of lanthanide diphthalocyanine 985
– – – of tin 413
– – – of zinc oxide 785
– – through metalorganic chemical vapor deposition
– – – of aluminum gallium arsenide 769
– – – of cadmium sulphide 989
– – – of cadmium zinc sulphide 989
– – – of gallium arsenide 101, 378, 483, 497, 693, 790
– – – of gallium phosphide 906
– – – of indium phosphide 369, 483, 691
– – – of mercury cadmium telluride 519, 552
– – – of III–V compounds 13
– – – of zinc sulphide 979
– – – theory of 693
Three–five (III–V) compounds 13, 680
Tin 413
– diselenide 649
– lead alloy 996
– selenide 649
Titanium
– carbide 871
Twinning 519, 533, 628, 756

Vapor growth technique
– by chemical transport
– – of chromium disilicides 127
– – of mercury cadmium telluride 933
– – of molybdenum oxides 708
– – of molybdenum sulphide 685
– – of niobium selenide iodide 234, 243
– – of zinc selenide 217
– by evaporation and condensation
– – of mercury (I) chloride 969
– – of zinc selenide 756
Vapor–liquid–solid growth
– of silicon nitride 383

Whisker growth
– of chromium silicides 127
– of silicon nitride 383
– of titanium carbide 871

Xenon 175

Yttrium
– barium aluminate 1010
– barium cuprate 465, 1002, 1010, 1019

Zinc
– organic 989
– oxide 363, 785
– selenide 217, 513, 756
– sulphide 979
Zirconia 96